

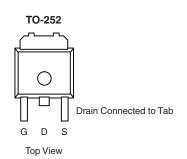
P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
- 60	0.170 at V _{GS} = - 10 V	- 10			
	0.280 at V _{GS} = - 4.5 V	- 8			

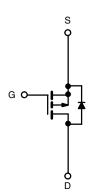
FEATURES

- TrenchFET® Power MOSFETs
- 175 °C Rated Maximum Junction Temperature





Ordering Information: SUD10P06-280L-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	15 1 _C = 25 °C, unit	ess otherwise no	iea	
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current (T. – 150 °C)	T _C = 25 °C	_	- 10	
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	I _D	- 7	
Pulsed Drain Current		I _{DM}	- 20	Α
Continuous Source Current (Diode Conduction)		I _S	- 10	
Avalanche Current		I _{AS}	- 10	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	5	mJ
Maximum Daylar Dissination	T _C = 25 °C	P _D	37	10/
Maximum Power Dissipation	T _A = 25 °C		2 ^a	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Junction-to-Ambient ^a	FR4 Board Mount	R _{thJA}	60	70	°C/W		
	Free Air		120	140			
Junction-to-Case	·	R _{thJC}	3.7	4.0			

Notes:

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.

a. Surface Mounted on FR4 board.



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SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min. Typ. ^a		Max.	Unit	
Static	•						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 60			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0	- 2.0	- 3.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ	
		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$			- 150		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 10			Α	
		V _{GS} = - 10 V, I _D = - 5 A			0.170	Ω	
Durin Course On Chata Basistanah	B	$V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}, T_J = 125 ^{\circ}\text{C}$			0.31		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A, T _J = 175 °C		0.375			
		V _{GS} = - 4.5 V, I _D = - 2 A		0.210	0.280	280	
Forward Transconductance ^b	9 _{fs}	V _{DS} = - 15 V, I _D = - 5 A		6		S	
Dynamic							
Input Capacitance	C _{iss}			635			
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		100		pF	
Reverse Transfer Capacitance	C _{rss}			30			
Total Gate Charge	Q_g			11.5	25		
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -10 \text{ A}$		3.5		nC	
Gate-Drain Charge	Q_{gd}			2		1	
Turn-On Delay Time ^c	t _{d(on)}			9	20		
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 3 Ω		16	20	- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong$ 10 A, V_{GEN} = - 10 V, R_G = 2.5 Ω		17	30		
Fall Time ^c	t _f	1 1		19	35		
Source-Drain Diode Ratings and Cha	aracteristics	T _C = 25 °C ^a			<u>. </u>		
Pulsed Current	I _{SM}				- 20	Α	
Forward Voltage ^b	V_{SD}	I _F = 10 A, V _{GS} = 0 V			- 1.3	٧	
Reverse Recovery Time	t _{rr}	I _F = 10 A, dl/dt = 100 A/μs		50	80	ns	

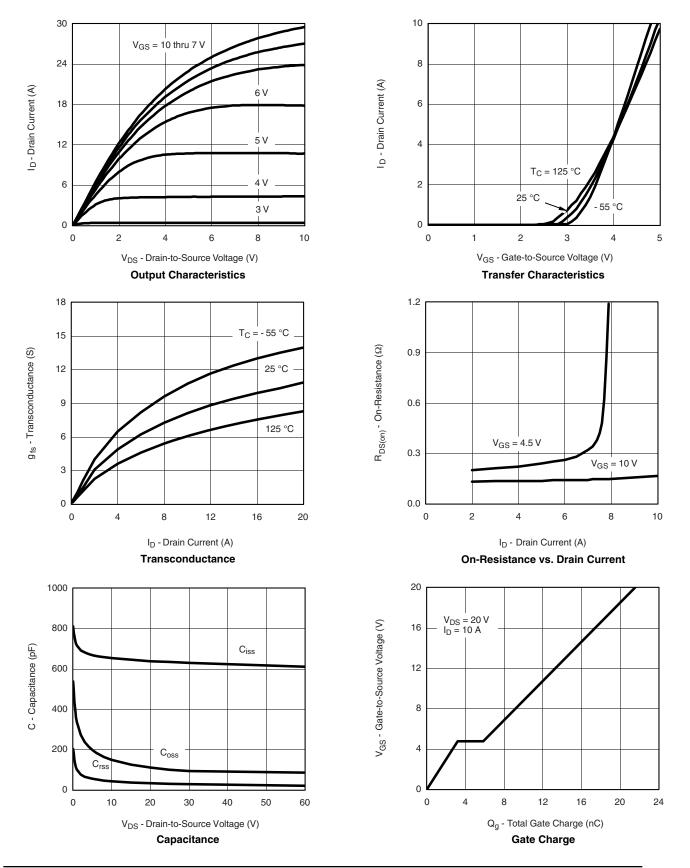
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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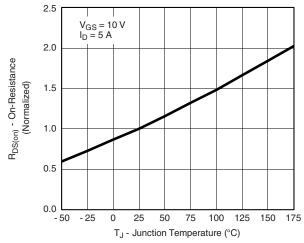
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



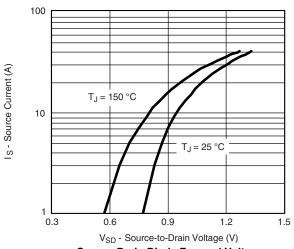


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

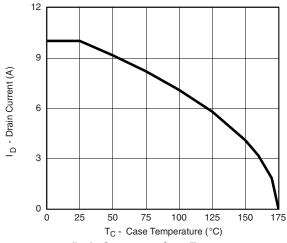


On-Resistance vs. Junction Temperature

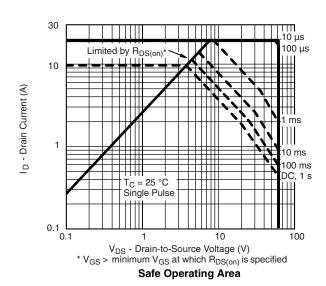


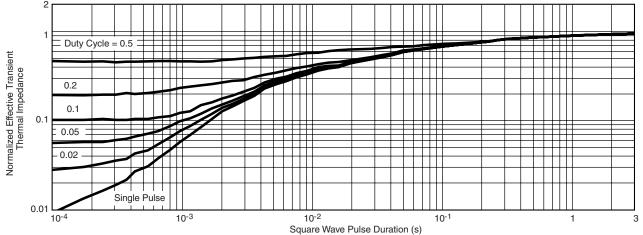
Source-Drain Diode Forward Voltage

THERMAL RATINGS



Drain Current vs. Case Temperature



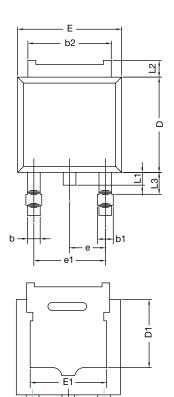


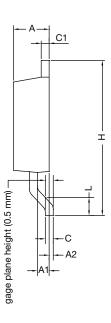
Normalized Thermal Transient Impedance, Junction-to-Case



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TO-252AA CASE OUTLINE





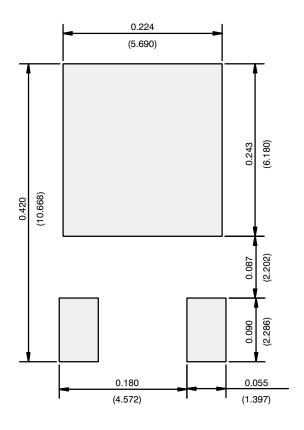
	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
A2	0.030	0.127	0.001	0.005
b	0.71	0.88	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.44	0.206	0.214
С	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.10	4.45	0.161	0.175
Е	6.48	6.73	0.255	0.265
E1	4.49	5.50	0.177	0.217
е	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
Н	9.65	10.41	0.380	0.410
L	1.40	1.78	0.055	0.070
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.040	0.060
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347				

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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